

Silicon NPN Power Transistors

2SC1520

DESCRIPTION

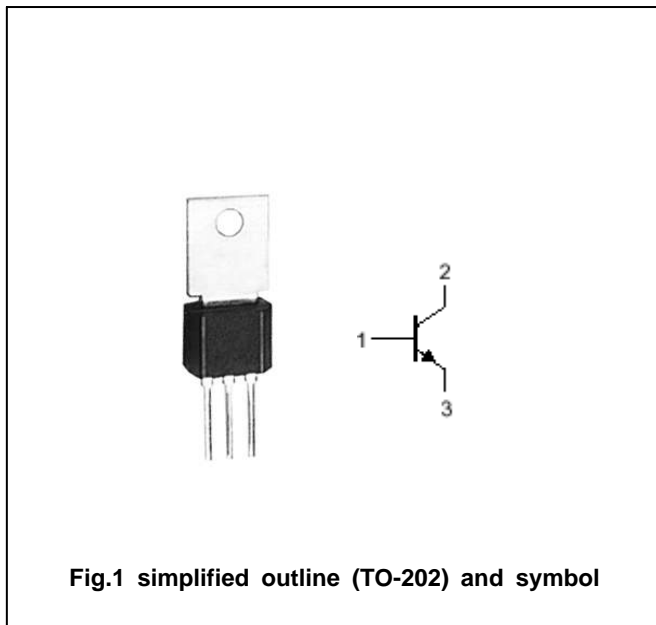
- With TO-202 package
- High voltage
- High transition frequency

APPLICATIONS

- For color TV chroma output and video output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	250	V
$V_{CEO}$	Collector-emitter voltage	Open base	250	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		0.2	A
$P_C$	Collector power dissipation	$T_a=25^{\circ}C$	1.0	W
		$T_C=25^{\circ}C$	10	
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =5mA			2.0	V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA; I <sub>B</sub> =0	250			V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =150V ; I <sub>E</sub> =0			0.1	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =10mA ; V <sub>CE</sub> =10V	40		200	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =50V; f=1MHz			4.5	pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =10mA ; V <sub>CB</sub> =30V		80		MHz

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PACKAGE OUTLINE

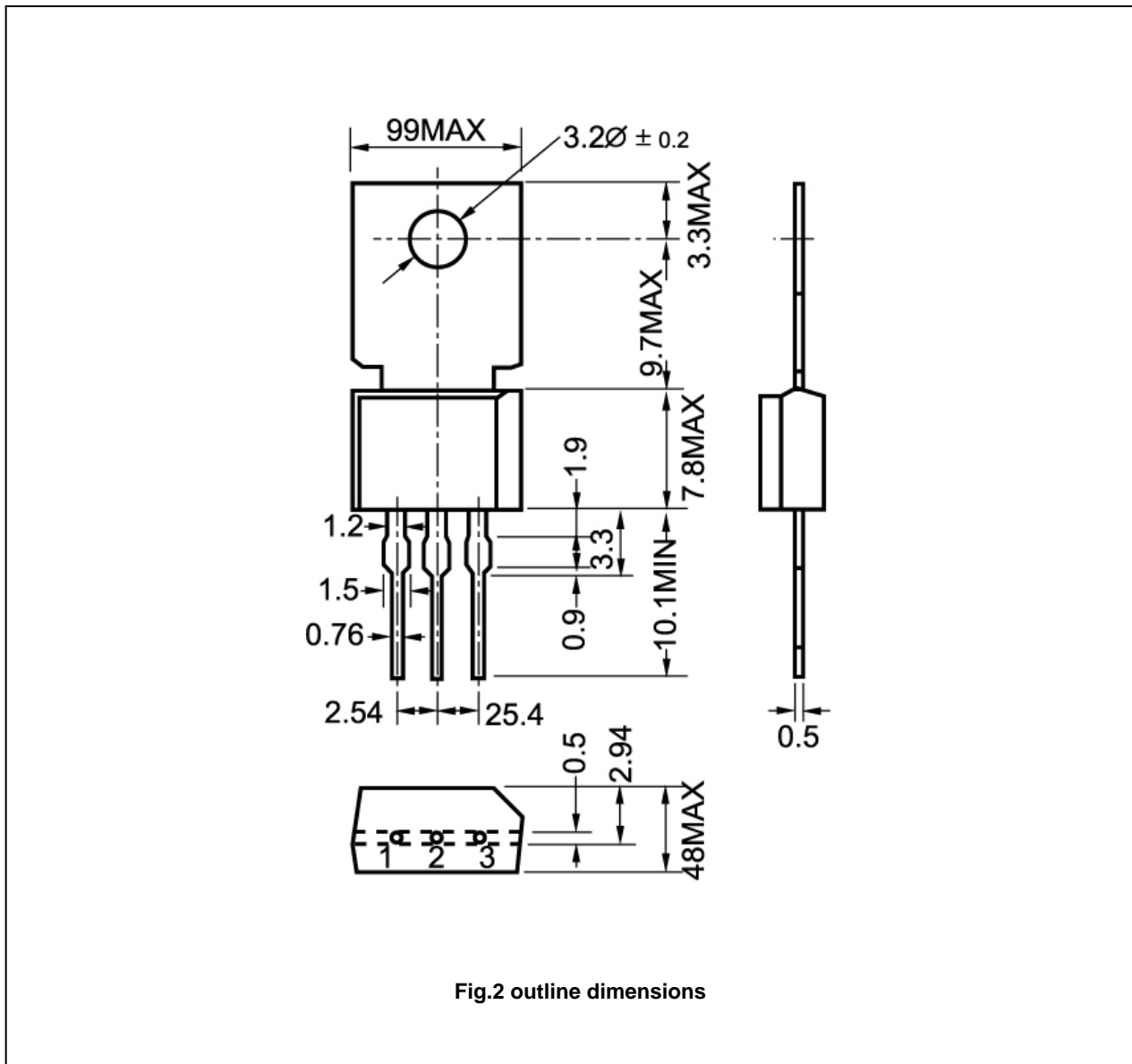


Fig.2 outline dimensions